

B 340D
 B 342D
 TRANSISTOR ARRAYS

The β 340D and β 342D each consist of four general purpose silicon n-p-n transistors on a common monolithic substrate. The transistors are well suited to a wide variety of low power applications in the DC through VHF range. They may be used as discrete transistors in conventional circuits, however, in addition, they provide the very significant inherent integrated circuit advantages of close electrical and thermal matching.

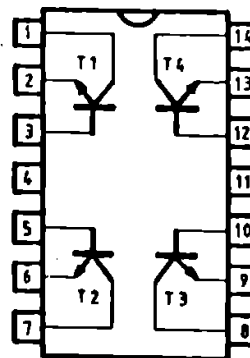
Features

- Operating temperature	-25 ... +70	oC
- Storage temperature	-25 ... +125	oC
- Collector-emitter breakdown voltage (VCEO) ...	min. 15	V
- Collector-base breakdown voltage (VCBO)	min. 20	V
- Collector-substrate breakdown voltage (VCSS) .	min. 30	V
- hFE (transistor T1)	β 340Dc, β 342Dc ... 56 ... 140	-
	β 340Dd, β 342Dd ... 112 ... 280	-
	β 340De, β 342De ... 224 ... 560	-
- hFE matching,	0.8 ... 1.25	-
- Base-emitter voltage matching ... β 340D	max. 5	mV
- Base current	max. 5	mA
- Collector current	max. 10	mA

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1. C1
2. E1
3. B1
4. Substrate
5. B2
6. E2
7. C2
8. C3
9. E3
10. B3
11. Substrate
12. B4
13. E4
14. C4

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PACKAGE TO-116 / TOP VIEW